

L Number	Hits	Search Text	DB	Time stamp
1	827	349/141	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:10
2	547	349/141 and (common counter) with (gate scanning)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:11
3	483	349/141 and common with (gate scanning)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:12
4	357	349/141 and common adj electrode with (gate scanning)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:12
5	153	349/141 and common adj electrode with parallel with (gate scanning)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:16
6	167	349/141 and common adj electrode with (gate scanning) adj line	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:16
7	130	(349/141 and common adj electrode with (gate scanning) adj line) and (ips in adj plane)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:35
8	2	6466289.pn.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 16:35

L Number	Hits	Search Text	DB	Time stamp
1	2757	257/59	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:59
2	194	257/59 and semiconductor same light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 08:52
3	2	(257/59 and semiconductor same light adj (intercept\$3 shield\$3)) and pixel with spac\$3 with common	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 08:52
4	151	257/59 and semiconductor with light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:05
5	43	(257/59 and semiconductor same light adj (intercept\$3 shield\$3)) and common adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 08:53
6	33	(257/59 and semiconductor with light adj (intercept\$3 shield\$3)) and common adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:06
7	2295	257/72	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:05
8	114	257/72 and semiconductor with light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:12
9	26	(257/72 and semiconductor with light adj (intercept\$3 shield\$3)) and common adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:06
10	317	257/294	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:25
11	42	257/294 and semiconductor with light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:59
12	1767	257/350	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:25
13	46	257/350 and semiconductor with light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 09:25
14	871	438/29	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/18 10:01

15	6	438/29 and semiconductor with light adj (intercept\$3 shield\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:00
16	9	438/29 and semiconductor same light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:01
17	1109	438/30	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:10
18	63	438/30 and semiconductor same light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:02
19	49	438/30 and semiconductor with light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:11
20	1788	438/149	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:21
21	43	438/149 and semiconductor with light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:21
22	292	438/161	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:21
23	14	438/161 and semiconductor with light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:22
24	14	438/161 and semiconductor same light adj (intercept\$3 shield\$3)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2004/06/18 10:22